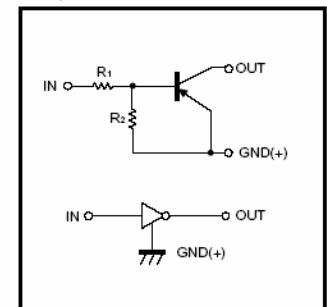


## Features

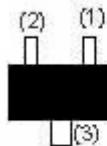
1. Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
2. The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
3. Only the on/off conditions need to be set for operation, making device design easy.

● Equivalent circuit



## PIN CONNECTIONS AND MARKING

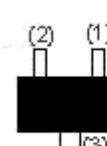
DTA114YE


 1.IN  
2.GND  
3.OUT

SOT-523

Addreviated symbol: 54

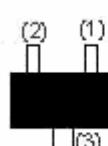
DTA114YUA


 1.IN  
2.GND  
3.OUT

SOT-323

Addreviated symbol: 54

DTA114YKA


 1.IN  
2.GND  
3.OUT

SOT-23-3L

Addreviated symbol: 54

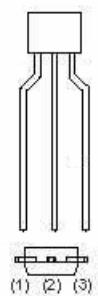
DTA114YCA


 1.IN  
2.GND  
3.OUT

SOT-23

Addreviated symbol: 54

DTA114YSA


 1.GND  
2.OUT  
3.IN

TO-92S

**Absolute maximum ratings(Ta=25°C)**

Digital Transistor(PNP)

Parameter	Symbol	Limits (DTA114Y□ )					Unit				
		E	UA	KA	CA	SA					
<b>Supply voltage</b>	V <sub>CC</sub>	-50					V				
<b>Input voltage</b>	V <sub>IN</sub>	-40to+6					V				
<b>Output current</b>	I <sub>O</sub>	-70					mA				
	I <sub>C(Max.)</sub>	-100					mA				
<b>Power dissipation</b>	P <sub>C</sub>	150	200		300		mW				
<b>Junction temperature</b>	T <sub>j</sub>	150					°C				
<b>Storage temperature</b>	T <sub>stg</sub>	-55 to+ 150					°C				

**Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
<b>Input voltage</b>	V <sub>I(off)</sub>			-0.3	V	V <sub>CC</sub> =-5V ,I <sub>O</sub> =-100μA
	V <sub>I(on)</sub>	-1.4				V <sub>O</sub> =-0.3V ,I <sub>O</sub> =-1mA
<b>Output voltage</b>	V <sub>O(on)</sub>			-0.3	V	I <sub>O</sub> /I <sub>I</sub> =-5mA/-0.25mA
<b>Input current</b>	I <sub>I</sub>			-0.88	mA	V <sub>I</sub> =-5V
<b>Output current</b>	I <sub>O(off)</sub>			-0.5	μA	V <sub>CC</sub> =-50V ,V <sub>I</sub> =0
<b>DC current gain</b>	G <sub>I</sub>	68				V <sub>O</sub> =-5V ,I <sub>O</sub> =-5mA
<b>Input resistance</b>	R <sub>I</sub>	7	10	13	KΩ	
<b>Resistance ratio</b>	R <sub>2</sub> /R <sub>1</sub>	3.7	4.7	5.7		
<b>Transition frequency</b>	f <sub>T</sub>		250		MHz	V <sub>O</sub> =-10V ,I <sub>O</sub> =5mA,f=100MHz

**Typical Characteristics**
**●Electrical characteristic curves**
